## IN THE CLAIMS

Claims 1-2 Cancelled.

- 3. (Currently Amended) The cross-coupled inverter of claim 222 wherein the body and the drain of the first NFET are coupled to the body and the drain of the first PFET.
- 4. (Currently Amended) The cross-coupled inverter of claim 222 wherein the body and the drain of the second NFET are coupled to the body and the drain of the second PFET.
- 5. (Currently Amended) The cross-coupled inverter of claim <u>222</u> wherein the first NFET, the second NFET, the first PFET and the second PFET each comprises a silicon-on-insulator metal-oxide semiconductor field effect transistor.
- 6. (Currently Amended) The cross-coupled inverter of claim 222 wherein the first NFET, the second NFET, the first PFET and the second PFET each comprises a triple-well metal-oxide-semiconductor field effect transistor.

Claims 7-10 Cancelled.

11. (Currently Amended) The cross-coupled inverter of claim 1023 wherein the drain of the second NFET is coupled to the drain of the second PFET.

- 12. (Currently Amended) The cross-coupled inverter of claim 1023 wherein the drain of the second NFET is coupled to the drain of the second PFET.
- 13. (Currently Amended) The cross-coupled inverter of claim 1023 wherein the first NFET, the second NFET, the first PFET and the second PFET each comprises a silicon-on-insulator metal-oxide-semiconductor field effect transistor.
- 14. (Currently Amended) The cross-coupled inverter of claim 1023 wherein the first NFET, the second NFET, the first PFET and the second PFET each comprises a triple-well metal-oxide-semiconductor field effect transistor.

Claims 15-16 Cancelled.

- 17. (Currently Amended) The method of claim 1624 further comprising coupling the body and the drain of the first NFET to the body of the drain of the first PFET.
- 18. (Currently Amended) The method of claim 1624 further comprising coupling the body and the drain of the second NFET to the body of the drain of the second PFET.
- 19. (Currently Amended) The method of claim 1624 wherein coupling the body and the drain of the first NFET together comprises resistively coupling the body and the drain of the first NFET together.

20. (Cancelled)

21. (Currently Amended) The method of claim 1524 wherein coupling the body of at least one of the first NFET, the second NFET, the first PFET and the second PFET so as to form a feedback path comprises:

capacitively coupling the body and the drain of the first NFET; capacitively coupling the body and the drain of the first PFET; capacitively coupling the body and the drain of the second NFET; and capacitively coupling the body and the drain of the second PFET.

Please add the following new claims:

22. (New) A cross-coupled inverter comprising:

a first inverter circuit including a first NFET coupled to a first PFET, the first NFET having a body and drain being coupled one to another, and the first PFET having a body and drain coupled one to another; and

a second inverter circuit cross-coupled with the first inverter circuit at a plurality of nodes, the second inverter circuit including a second NFET coupled to a second PFET, the second NFET having a body and a drain coupled one to another, and the second PFET having a body and drain coupled one to another;

wherein the body of at least one of the first NFET, the second NFET, the first PFET and the second PFET is coupled so as to form a feedback path that reduces

discharging at one or more of the plurality of nodes in response to a soft error event at the cross-coupled inverter.

## 23. (New) A cross-coupled inverter comprising:

a first inverter circuit including a first NFET coupled to a first PFET, the first NFET having a body and drain being coupled one to another with a first capacitor, and the first PFET having a body and drain coupled one to another with a second capacitor; and

a second inverter circuit cross-coupled with the first inverter circuit at a plurality of nodes, the second inverter circuit including a second NFET coupled to a second PFET, the second NFET having a body and a drain coupled one to another with a third capacitor, and the second PFET having a body and drain coupled one to another with a fourth capacitor;

wherein the body of at least one of the first NFET, the second NFET, the first PFET and the second PFET is coupled so as to form a feedback path that reduces discharging at one or more of the plurality of nodes in response to a soft error event at the cross-coupled inverter.

24. (New) A method of forming a cross-coupled inverter, the method comprising the steps of:

providing a cross-coupled inverter circuit having:

a first inverter circuit including a first NFET coupled to a first PFET, the first NFET and first PFET each having a body and drain; and

a second inverter circuit cross-coupled with the first inverter circuit at a plurality of nodes, the second inverter circuit including a second NFET coupled to a second PFET, the second PFET and NFET having a body and a drain;

coupling the body and the drain of the first NFET together;
coupling the body and the drain of the second NFET together;
coupling the body and the drain of the second NFET together;
coupling the body and the drain of the second PFET together; and
coupling the body of at least one of the first NFET, the second NFET, the first
PFET and the second PFET is coupled so as to form a feedback path that reduces
discharging at one or more of the plurality of nodes in response to a soft error event at
the cross-coupled inverter.

## **CLAIM REJECTIONS**

Claims 1, 7-9, 15 and 20 were rejected for various reasons in connection with 35 U.S.C. sections 102 and 103(a). Claims 1, 7-9, 15, and 20 have been cancelled, thus rendering the rejections moot.